

**EAST Search History****EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4845	:257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/23 13:09
S2	660	:257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/01 14:37
S3	2	:257/e29.145.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/01 14:37
S4	34	(:"4591848"   "5132819"   "5457474"   "5477073"   "5567959"   "5644147"   "5807772"   "5814834"   "5818070"   "5821137"   "5834797"   "5917199"   "5917221"   "5929527"   "5956011"   "6010923"   "6037924"   "6072193"   "6081131"   "6150283"   "6153893"   "6197624"   "6198133"   "6204519"   "6207971"   "6215154"   "6380011"   "6392628"   "6396078"   "6462723"   "6512271"   "6569716"   "6603453"   "6608613"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/05/01 14:38
S6	40	:(light near shield) same (titanium near oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 11:39

S7	2	("20020089616").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 11:46
S10	2	("20010034088").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 16:36
S11	212	("thin film transistor" or tft) same ((liquid near crystal) near (electroluminescent or el))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/05 10:16
S12	3824	257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/05 10:54
S13	26	capacitor near electrode near copper	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/06 14:14
S14	13	(("20030143794") or ("6787407") or ("20010034088") or ("6821827") or ("20050054181") or ("20030219934") or ("6908796") or ("20020089616") or ("6587165")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/06 14:56
S15	376	257/e27.116.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 11:37
S16	3566	((SHUNPEI) near2 (YAMAZAKI)).INV.	US-PGPUB; USPAT	OR	ON	2008/11/03 11:41
S17	338	((SHUNPEI) near2 (YAMAZAKI)).INV. and ("droplet discharge" or "ink- jet")	US-PGPUB; USPAT	OR	ON	2008/11/03 11:42

S18	13	(("20070132377") or ("20070082443") or ("20070040971") or ("20070096096") or ("7176069") or ("7202497") or ("7192865")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 11:47
S19	8	(("5948705") or ("6221140") or ("6043149") or ("5706064")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 11:53
S20	2	"US 20070085938"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2008/11/03 12:18
S21	7	("4712874"   "5153753"   "5321535"   "5321538"   "5503932"   "5517343"   "5520855").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/03 12:37
S22	16	(("20020089616") or ("6365917") or ("5706064") or ("4389481") or ("5329390") or ("20010034088") or ("20010014528") or ("6461914")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 17:16
S23	2	"US 20070085938"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2008/11/03 19:07
S25	85	(copper near wiring) same (tft or "thin film transistor")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 19:22
S26	81	(amorphous near gate) same (tft or "thin film transistor")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 19:50
S27	4003	257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:18

S28	733	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S29	1461	257/e29.137.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S30	950	257/e29.273.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S31	203	257/e29.202.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S32	3	257/e29.145.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S33	944	257/e29.147.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S34	212	257/e31.096.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:20
S35	1699	257/e33.061.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:20

S36	365	257/e31.095.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:20
S37	458	("thin film transistor" or tft) same ((liquid near crystal or LCD) near (electroluminescent or el))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/15 18:39
S41	15	("thin film transistor" or tft) same (liquid near crystal or LCD) same (electroluminescent or el) same (insulat\$3 or dielectric) with (opening or recess or window or via or throughhole or trench)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/15 18:41
S42	36	("thin film transistor" or tft) near (liquid near crystal or LCD) near (electroluminescent or el)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/15 18:44
S43	198	("thin film transistor" or tft) same (liquid near crystal or LCD) same (electroluminescent or el) same (insulat\$3 or dielectric) with (metal or interconnect or conduct\$3 or via or plug)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 17:24
S44	251	("thin film transistor" or tft) same (liquid near crystal or LCD) same (electroluminescent or el) same (insulat\$3 or dielectric) same (metal or interconnect or conduct\$3 or via or plug)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 17:25
S45	4207	257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03

S46	808	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S47	1584	257/e29.137.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S48	1024	257/e29.273.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S49	217	257/e29.202.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S50	3	257/e29.145.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S51	1025	257/e29.147.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S52	218	257/e31.096.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S53	215	257/e33.061.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:04

S54	392	257/e31.095.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:04
S55	45	planariz\$5 near metal near plug	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:07
S56	4375	257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:29
S57	826	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:29
S58	1593	257/e29.137.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:29
S59	1124	257/e29.273.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S60	220	257/e29.202.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S61	3	257/e29.145.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30

S62	1029	:257/e29.147.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S63	221	:257/e31.096.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S64	279	:257/e33.061.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S65	402	:257/e31.095.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:31
S66	18	"alkyl cyanobiphenyl"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/10 15:09
S67	1	((triphenylamine near derivative) or "MTDATA") near insulat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/10 15:23
S68	1	((diamine near derivative) or (TPD)) near insulat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/10 15:27
S69	2	("6211067").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/02/10 16:05

S70	108	(luminesc\$4 near insulat\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/28 18:12
S71	658	257/349.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/28 20:20
S72	853	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/28 20:20
S73	445	("thin film transistor" or tft) same (insulat\$3 or dielectric) same (metal or interconnect or conduct\$3 or via or plug) same lithograph\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 13:41
S74	332	("thin film transistor" or tft) same (liquid near crystal or LCD) same (electroluminescent or el) same (insulat\$3 or dielectric) same (metal or interconnect or conduct\$3 or via or plug)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 13:42
S75	443	S73 not S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 13:42
S76	680	257/349.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 15:38
S77	876	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 15:38

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